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Inclosure	Material:

Metal

Overall Length:

0.330 inches

Overall Diameter:

0.875 inches

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact-darlington connected

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Collector

Mounting Method:

Unthreaded hole

Features Provided:

Hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

90.0 collector to emitter voltage/static/base open and 90.0 collector to base voltage, dc and 5.0 emitter to base voltage, dc

Current Rating Per Characteristic:

20.00 amperes source cutoff current and 0.50 amperes source cutoff current

Power Rating Per Characteristic:

150.0 watts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

External surfaces gold

Precious Material:

Gold

Terminal Type And Quantity:

2 pin and 1 case

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

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